

Description

The G10N10A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

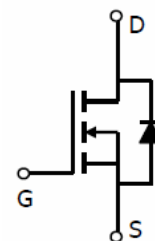
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V_{DSS}	$R_{DS(ON)}$ @10V (typ)	$R_{DS(ON)}$ @ 4.5V (typ)	I_D
100V	16m Ω	18m Ω	10A

- Special process technology for high ESD capability
- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- RoHS Compliant

Application

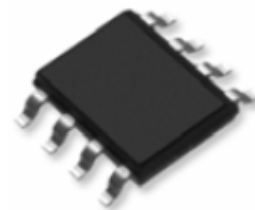
- DC/DC Primary Side Switch
- Telecom/Server
- Synchronous Rectification



Schematic diagram



Marking and pin assignment



SOP-8

Ordering Information

Part Number	Marking	Case	Packaging
G10N10A	G10N10A	SOP-8	4000pcs/Reel

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	10	A
Drain Current-Continuous($T_C=100^{\circ}\text{C}$)	$I_D(100^{\circ}\text{C})$	7	A
Pulsed Drain Current	I_{DM}	70	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	40	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

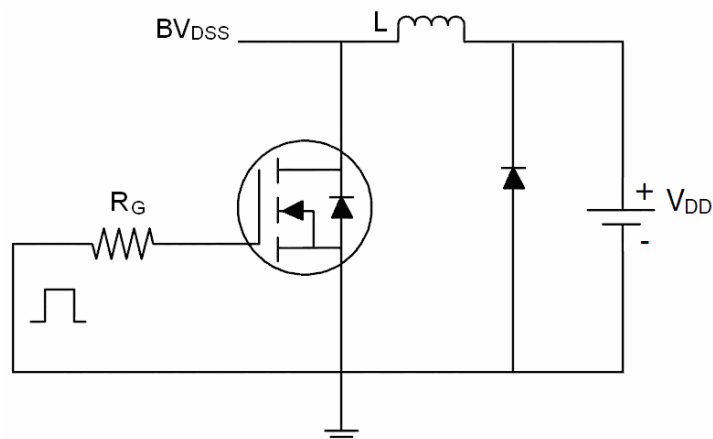
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.3	1.6	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	16	20	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 4.5V, I _D =10A	-	18	22	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =10A	-	26	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	2600	-	PF
Output Capacitance	C _{oss}		-	590	-	PF
Reverse Transfer Capacitance	C _{rss}		-	291	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =10A, R _L =5Ω, R _G =1Ω, V _{GS} =10V	-	13	-	nS
Turn-on Rise Time	t _r		-	14	-	nS
Turn-Off Delay Time	t _{d(off)}		-	25	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	I _D =10A, V _{DD} =50V, V _{GS} =10V	-	90	-	nC
Gate-Source Charge	Q _{gs}		-	16	-	nC
Gate-Drain Charge	Q _{gd}		-	24	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-	0.85	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	10	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 10A	-	33	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note3)	-	54	-	nC

Notes:

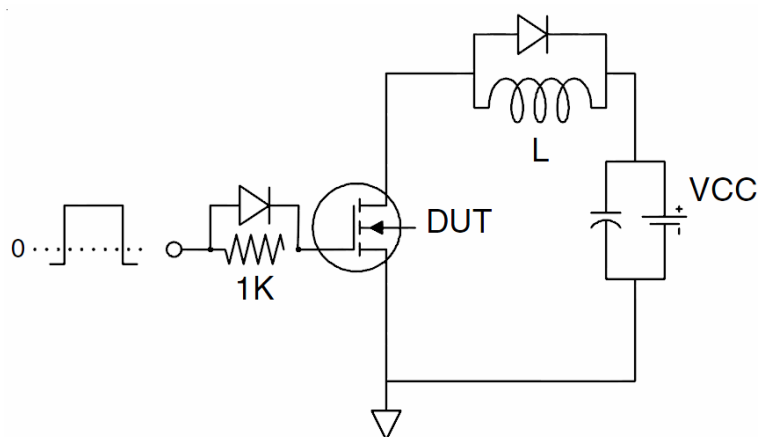
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Test Circuit

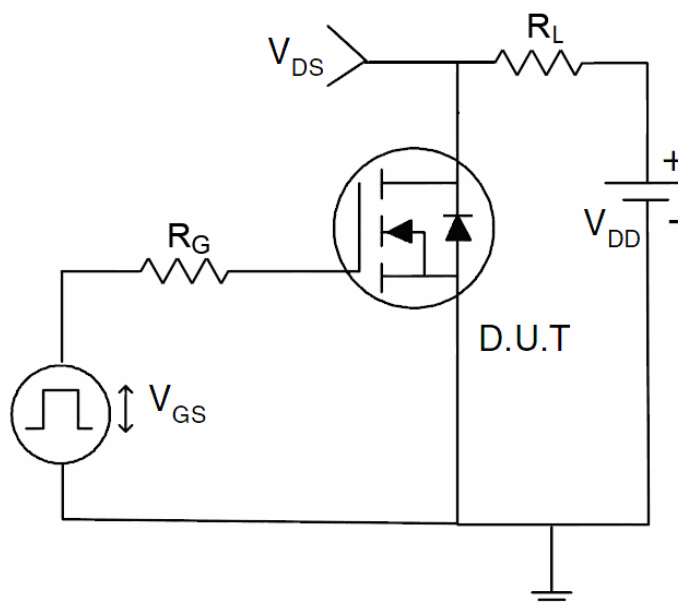
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

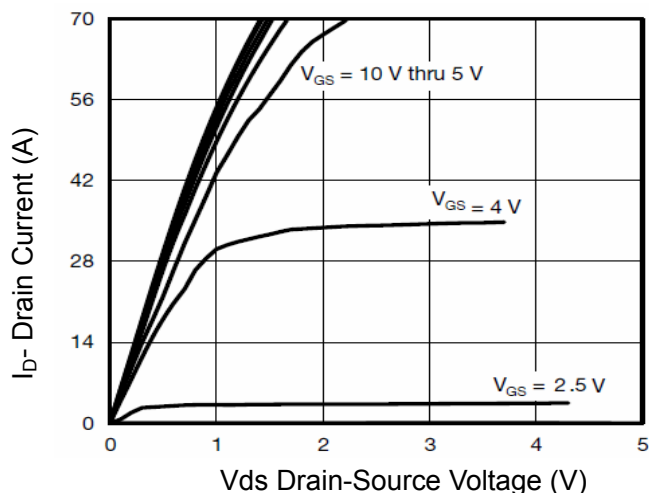


Figure 1 Output Characteristics

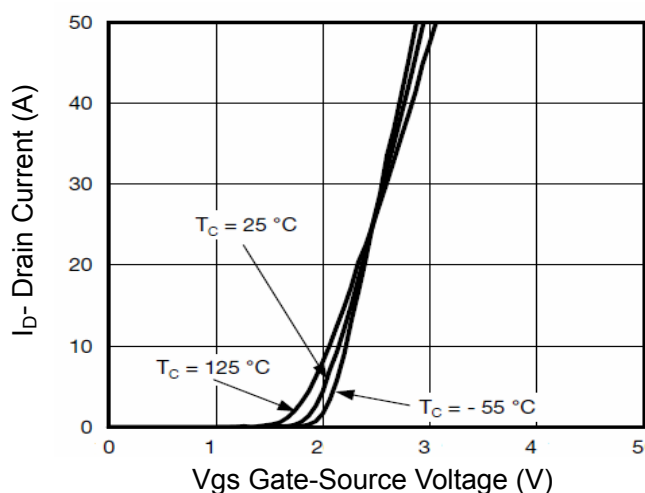


Figure 2 Transfer Characteristics

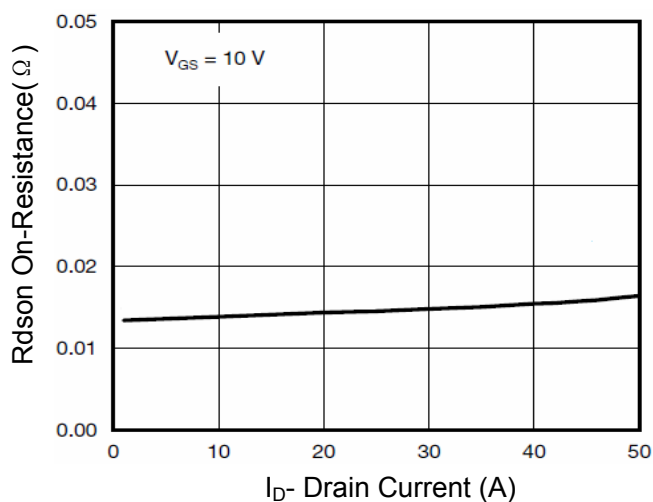


Figure 3 $R_{DS(on)}$ - Drain Current

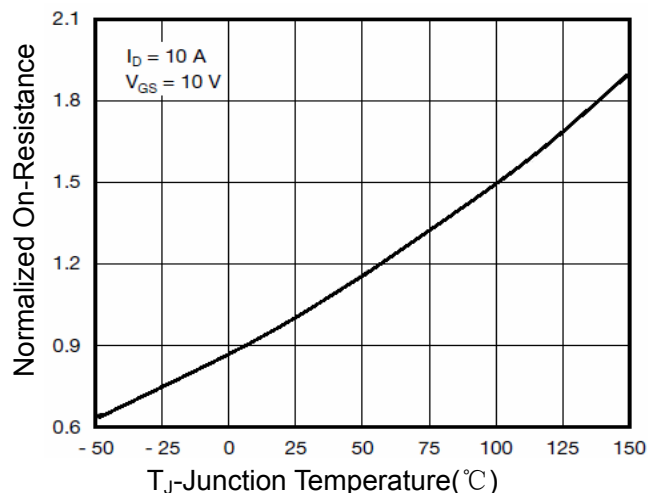


Figure 4 $R_{DS(on)}$ -Junction Temperature

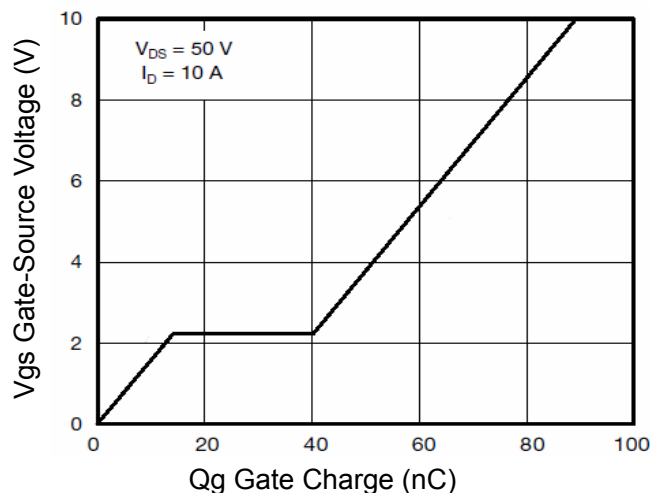


Figure 5 Gate Charge

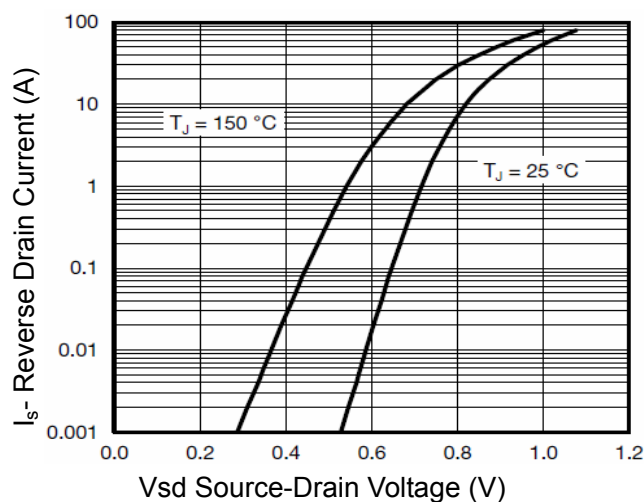


Figure 6 Source- Drain Diode Forward

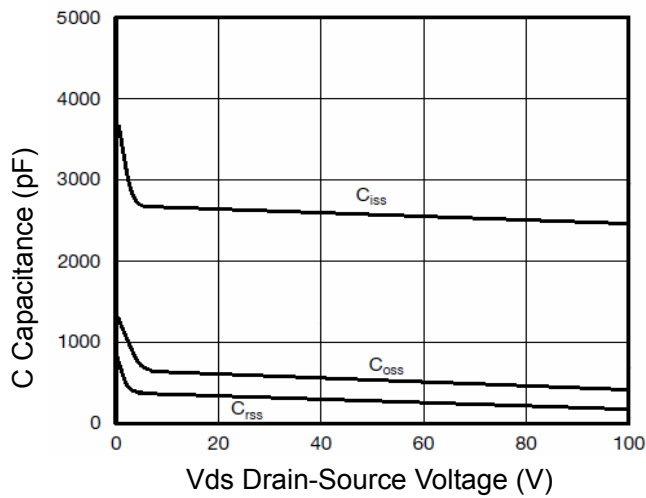


Figure 7 Capacitance vs Vds

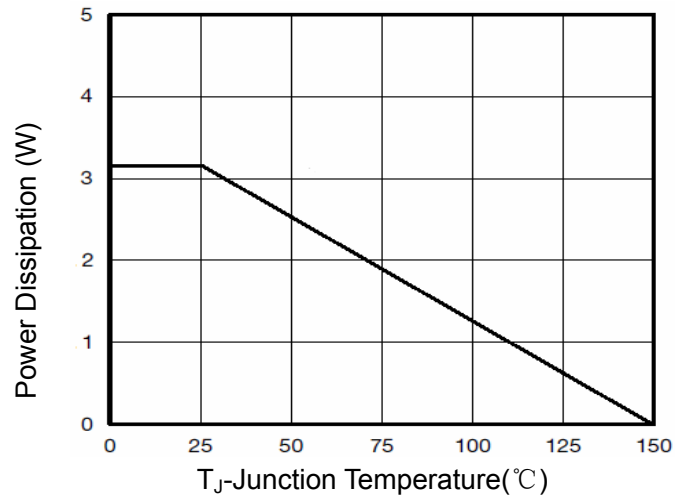


Figure 9 Power De-rating

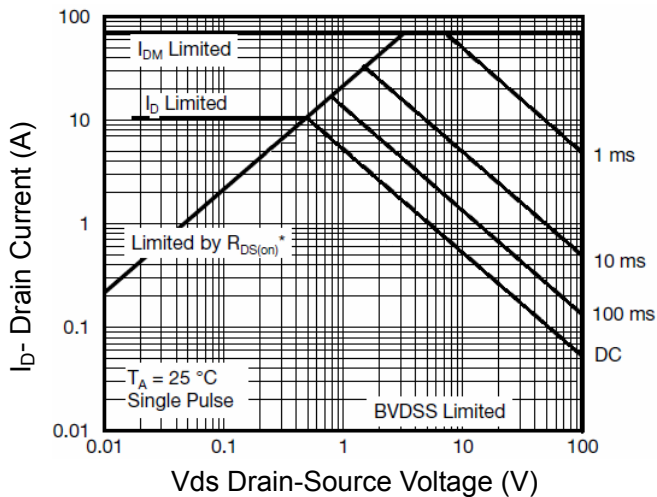


Figure 8 Safe Operation Area

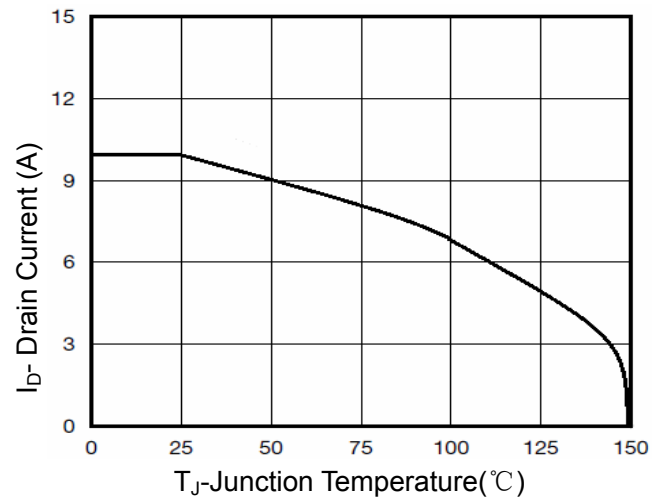


Figure 10 Current De-rating

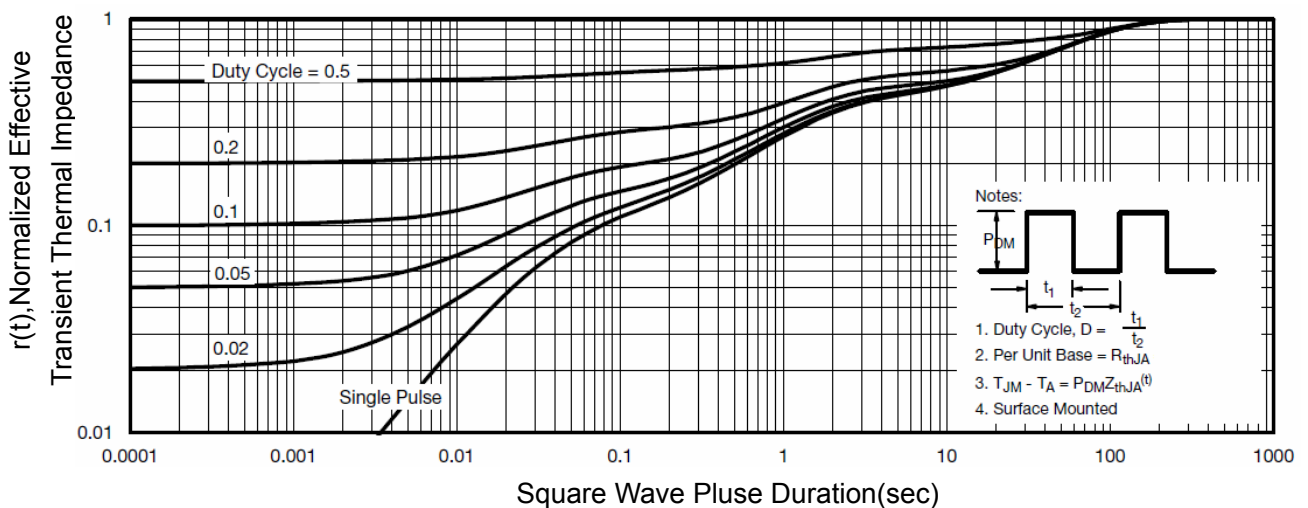
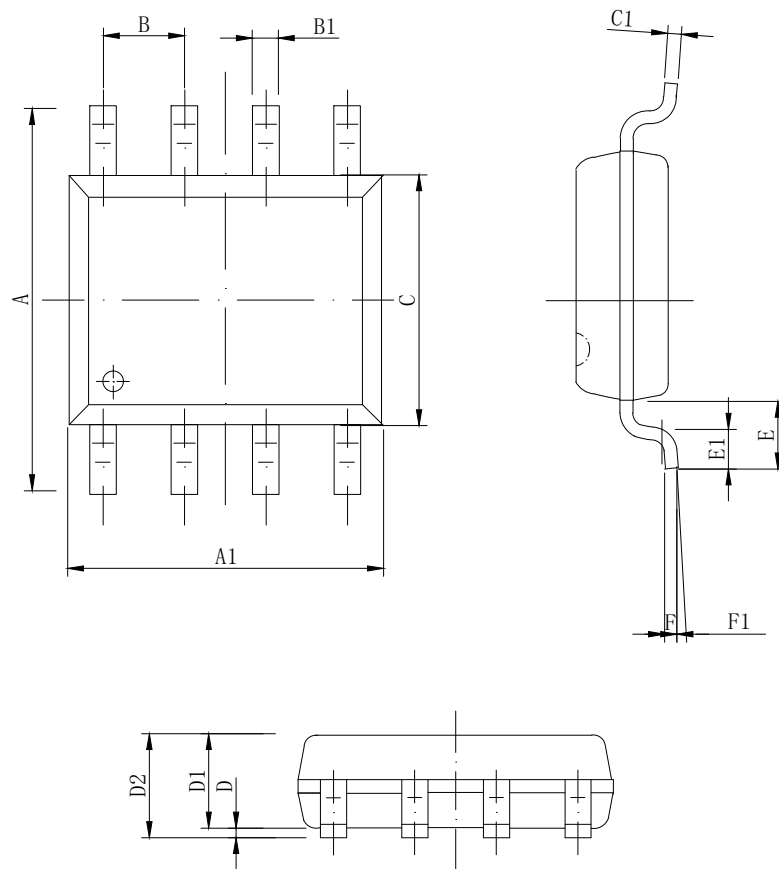


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package information



DIM	MIN	NOM	MAX
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 ^ 8x	0.40 ^ 8x	0.45 ^ 8x
C	3.780	3.880	3.980
C1	-	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
E	1.060 REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°

All Dimensions in mm